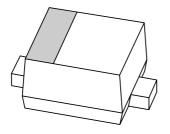
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2005EBLow V_F MEGA Schottky barrier diode

Product specification Supersedes data of 2003 Feb 20 2003 Apr 04





Low V_F MEGA Schottky barrier diode

PMEG2005EB

FEATURES

Forward current: 0.5 AReverse voltage: 20 V

• Very low forward voltage

· Guard ring protected

• Ultra small SMD package.

APPLICATIONS

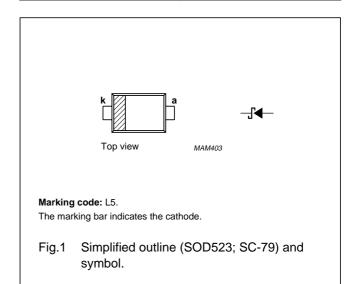
- Ultra high-speed switching
- · Voltage clamping
- · Protection circuits
- · Low current rectification
- Low power consumption applications (e.g. handheld devices).

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION	
1	cathode	
2	anode	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	TER CONDITIONS		MAX.	UNIT
V _R	continuous reverse voltage		_	20	V
I _F	continuous forward current		_	500	mA
I _{FRM}	repetitive peak forward current	$t_p = 1 \text{ ms}; \ \delta \le 0.25$	_	3.5	Α
I _{FSM}	non-repetitive peak forward current	t = 8 ms square wave	_	6	А
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

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PMEG2005EB

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2			
		I _F = 0.1 mA	120	180	mV
		I _F = 1 mA	180	240	mV
		I _F = 10 mA	245	290	mV
		I _F = 100 mA	320	380	mV
		I _F = 500 mA	430	480	mV
I _R	continuous reverse current	V _R = 10 V; see Fig.3; note 1	7	30	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$; see Fig.4	24	30	pF

Note

1. Pulsed test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	400	K/W

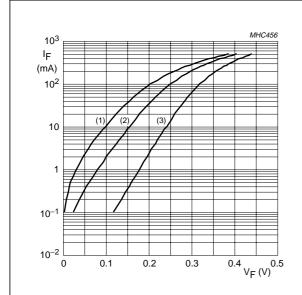
Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

Low V_F MEGA Schottky barrier diode

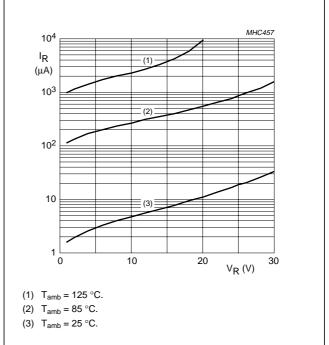
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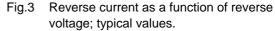
GRAPHICAL DATA



- (1) $T_{amb} = 125 \,^{\circ}C$.
- (2) $T_{amb} = 85 \,^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.





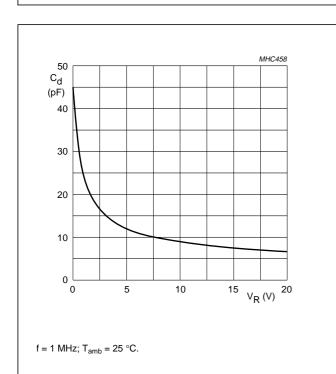


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

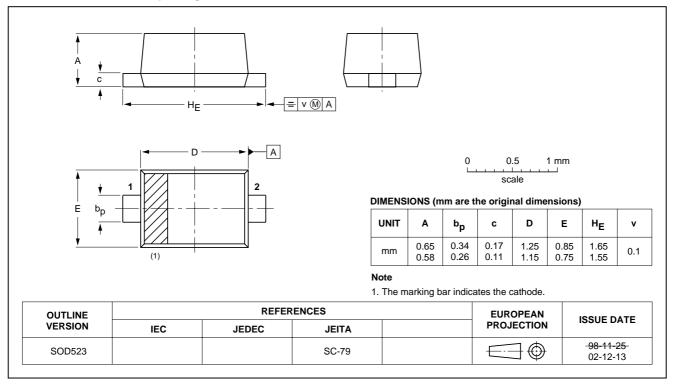
Low V_F MEGA Schottky barrier diode

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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD523



Low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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